University of California
College of Engineering
Department of Electrical Engineering and Computer Sciences

EECS 40 Fall 2003
Introduction to Microelectronic Circuits Prof. King

FINAL EXAMINATION

December 10, 2003

Time allotted: 2 hours 50 minutes (170 minutes)

Name: _____ , _____
(print) **Last** **First**

Signature: _____ **STUDENT ID#:** _____

1. This is a **CLOSED BOOK** exam. However, you may use 3 sheets of notes and a calculator.
2. **SHOW YOUR WORK or REASONING** on this exam.
   (Make your methods clear to the grade.)
3. **Write your answers clearly (legibly) in the spaces (lines, boxes, or plots) provided.**
4. Remember to specify the units on answers whenever appropriate.

SCORE: 1 _____ /20

2 _____ /20

3 _____ /20

4 _____ /20

5 _____ /20

6 _____ /20

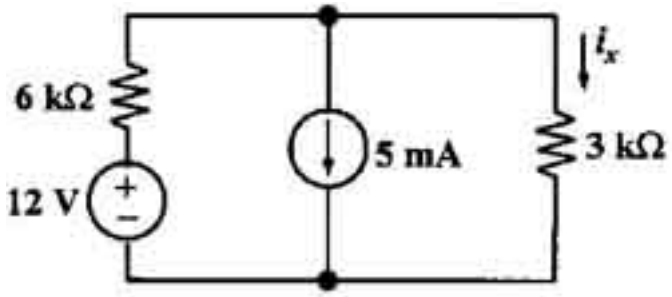
7 _____ /20

8 _____ /10

Total: _____ /150

<u>Problem 1</u>: Circuit Analysis and Equivalent Circuits [20 points in total]

a) Consider the following circuit:



i) Use a source transformation in order to fund $\mathbf{i_x}$. **[6 pts]**

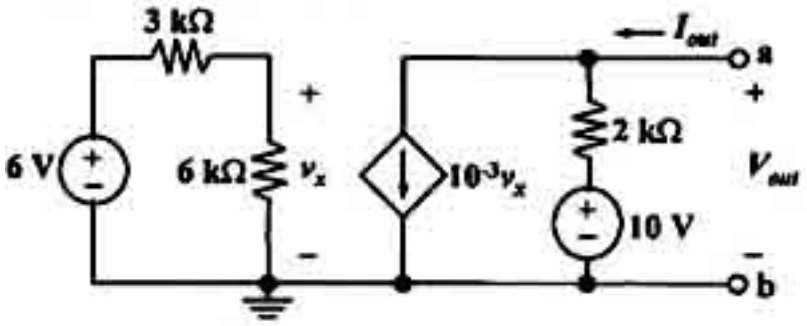
i_x = _____

ii) What is the power developed/absorbed by the 5mA current source? **[3 pts]**

Power = _____
[developed/absorbed]
(circle the correct choice)

Problem 1 (continued)

b) Consider the following circuit:

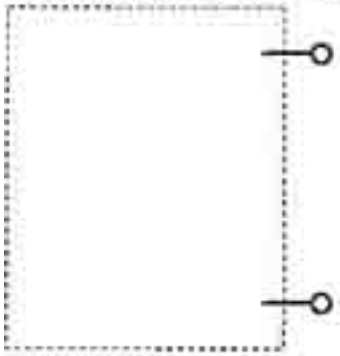


i) Find V_{out}. **[6 pts]**

V_{out} = _____

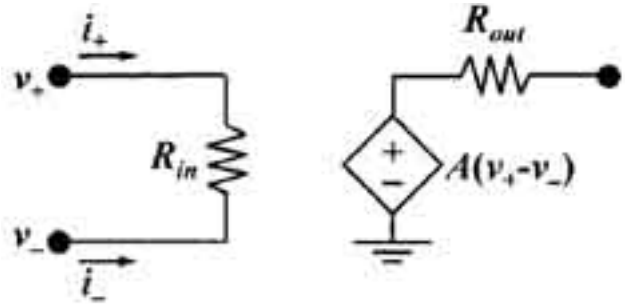
ii) Draw the Thevenin Equivalent circuit **[5 pts]**

Thevenin Equivalent Circuit:



<u>Problem 2</u>: Op Amp Circuit [20 points in total]

a) The following is the circuit model for an op amp circuit operating in its linear region:

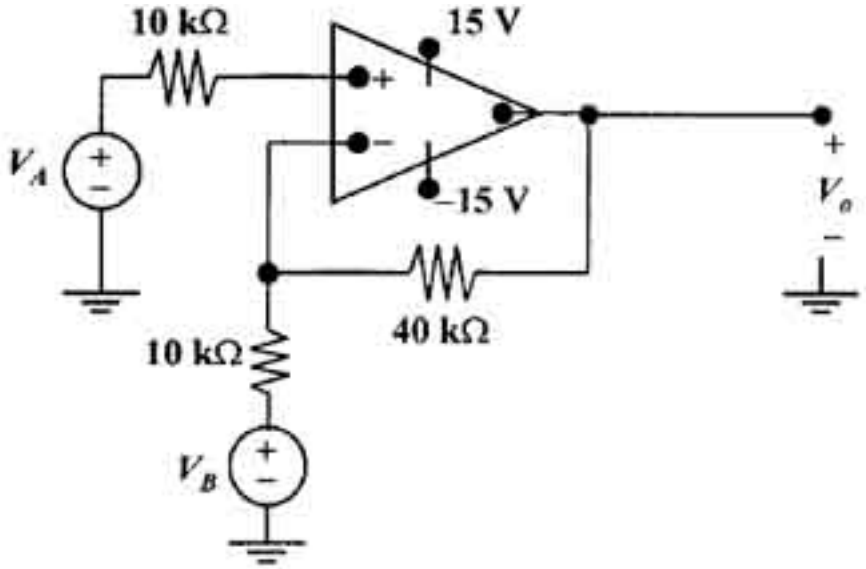


Typically, R_{in} is very large (~1-MΩ), A is very large (>10^4), and R_{out} is very small (<100Ω).

What type of feedback is used in an op amp circuit, in order to ensure that the op amp will operate in its linear region? Illustrate (with a simple diagram) how this is achieved. **[5pts]**

Problem 2 (continued)

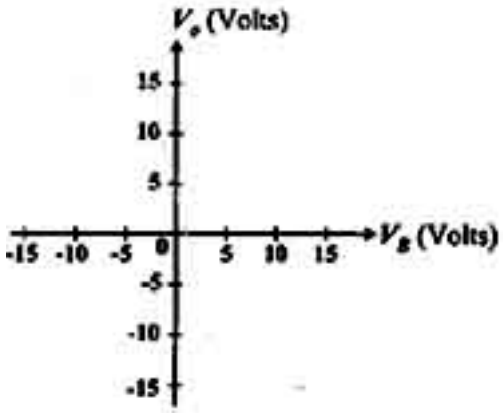
b) Consider the following op amp circuit below. You can assume that the op amp is ideal.



i) Find an expression for V_o, using superposition. **[10pts]**

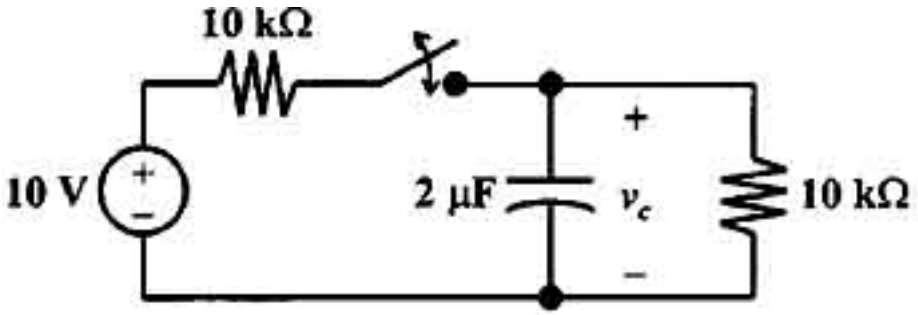
V_0 = _____

ii) Suppose V_A is fixed at 1 Volt. PlotV_0 vs V_B [5 pts]



Problem 3: **First –Order Circuits [20 points in total]**

In the circuit below, the switch is open for all t<0. The switch is closed at t = 0, and then it is open again at t = 10ms.



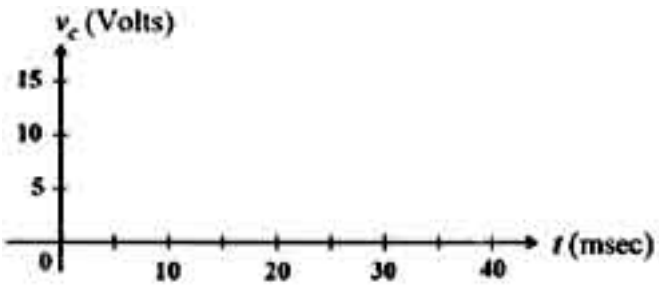
i) Write an equation for $v_c(t)$, for $0 \le t \le 10$ms. **[8 pts]**

$0 \le t \le 10$ms: $v_c(t)$ = _____

ii) Write an equation for $v_c(t)$, for t>10ms. **[8pts]**

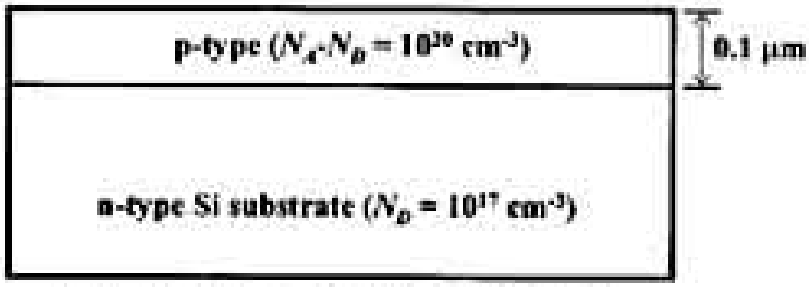
t> 10ms: $v_c(t)$ = _____

iii) Sketch $v_c(t)$ for t>0 **[4pts]**



Problem 4: pn junctions; diode [20 points in total]

a) Consider a pn junction formed in the surface of an n-type silicon wafer maintained at T = 300K. The p and n regions are uniformly doped, as indicated in the figure below:



Schematic cross-sectional view of pn junction

In the p-type region, the electron mobility is 100cm^2/V s and the hole mobility = 50cm^2/V s

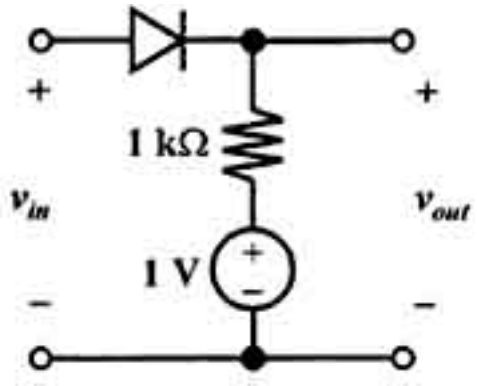
i) Estimate the sheet resistance of the p-type region **[6 pts]**
(Use the following values of constants: q = 1.6×10^{-19}C, n_i = 10^{10} cm^{-3})

Sheet resistance = _____

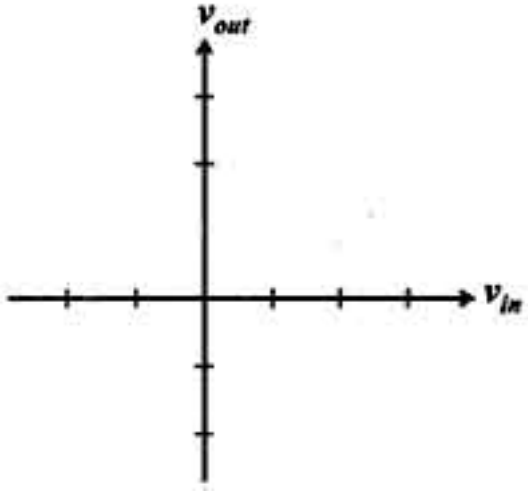
ii) Suppose the p-type region values serves as the drain region of a p-channel MOSFET in a CMOS inverter, and that the n-type substrate is therefore biased at the power-supply voltage V_{DD}. How will the pn-junction capacitance change as PMOSFET is turned on (so that the drain bias is changed from 0V to V_{DD})? Explain briefly. **[4 pts]**

Problem 4 (continued)

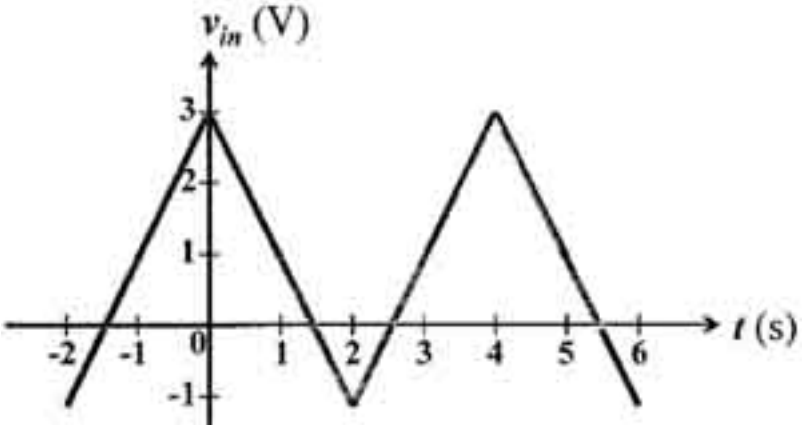
b) Consider the diode circuit below. Assume the diode is a perfect rectifier.



i) Plot v_{out} vs. v_{in} **[5 pts]**



iii) Sketch v_{out} for the given $v_{in(t)}$, using the same axes. **[5pts]**



Problem 5: MOSFET [20 points in total]

a) Consider an NMOSFFET with parameters W = 1μm, L = 0.1μm, $k_n' = 10^{-3}A/V^2$, $V_T = 0.5V$, biased at $V_{GS} = V_{DD} = 1V$. The areal gate capacitance $C_{OX} = 3\times10^{-6}F/cm^2$.

i) Accurately sketch the I_D vs. V_{DS} characteristic in the range $0 \leq V_{DS} \leq 1V$, neglecting velocity saturation and channel-length modulation. Indicate the numerical values for the saturation voltage (V_{DSAT}) and current (I_{DSAT}). **[6 pts]**

ii) Estimate the effective resistance of this MOSFET (for digital circuit applications). (Again, assume that velocity saturation and channel-length modulation can be neglected. **[3 pts]**

ii) On the same plot in part (i) above, accurately sketch and label the I_D vs. V_{DS} characteristic, taking into account that the electron velocity in the MOSFET channel saturates at 10^7cm/s**.** **[5 pts]**

Problem 5 (continued)

b) High drive current (I_{DSAT}) is desirable for reduced equivalent resistance, to achieve smaller propagation delay to allow higher-speed circuit operation. Indicate in the table below how you would adjust various MOSFET parameters so as to increase I_{DSAT}. Briefly describe the tradeoff or disadvantage involved, if any, for each. (For example, the answer for gate length L is given.) **[6 pts]**

MOSFET Parameter	To increase I_{DSAT}, parameter must be	Associated tradeoff or disadvantage
Gate length L	decreased	Subthreshold leakage current increases, so that static power dissipation increases
Threshold voltage V_T		
Channel width W		

Problem 6: Logic Circuits [20 points in total]

a) Given the following truth table for the logic function **F**:

A	B	F
0	0	1
0	1	0
1	0	1
1	1	1

i) Write a simple logic expression for **F**. **[2 pts]**

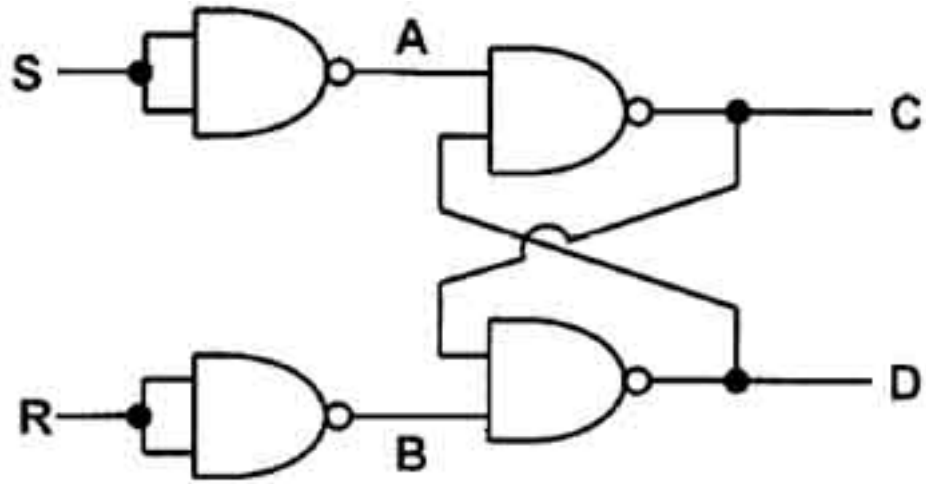
F = _____

iii) Implement the function **F,** using only 2-input NAND gates. **[5 pts]**

Logic circuit for F:

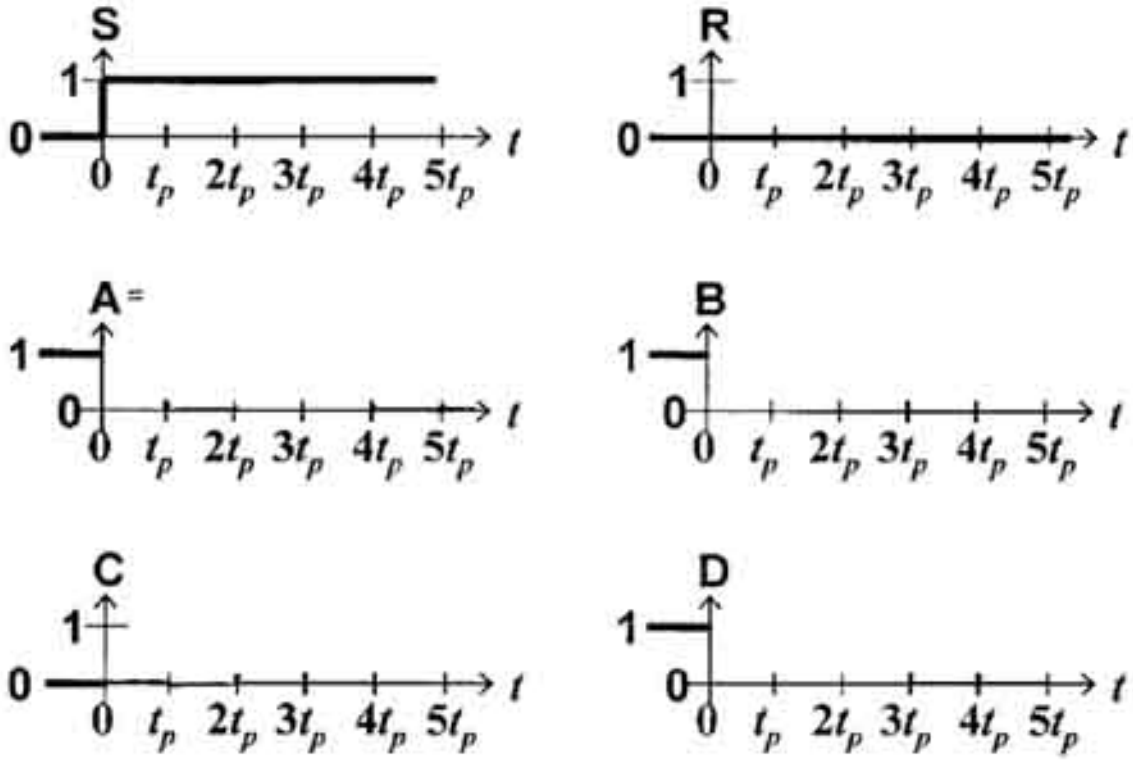
Problem 6 (continued)

b) Consider the S-R flip-flop circuit below:

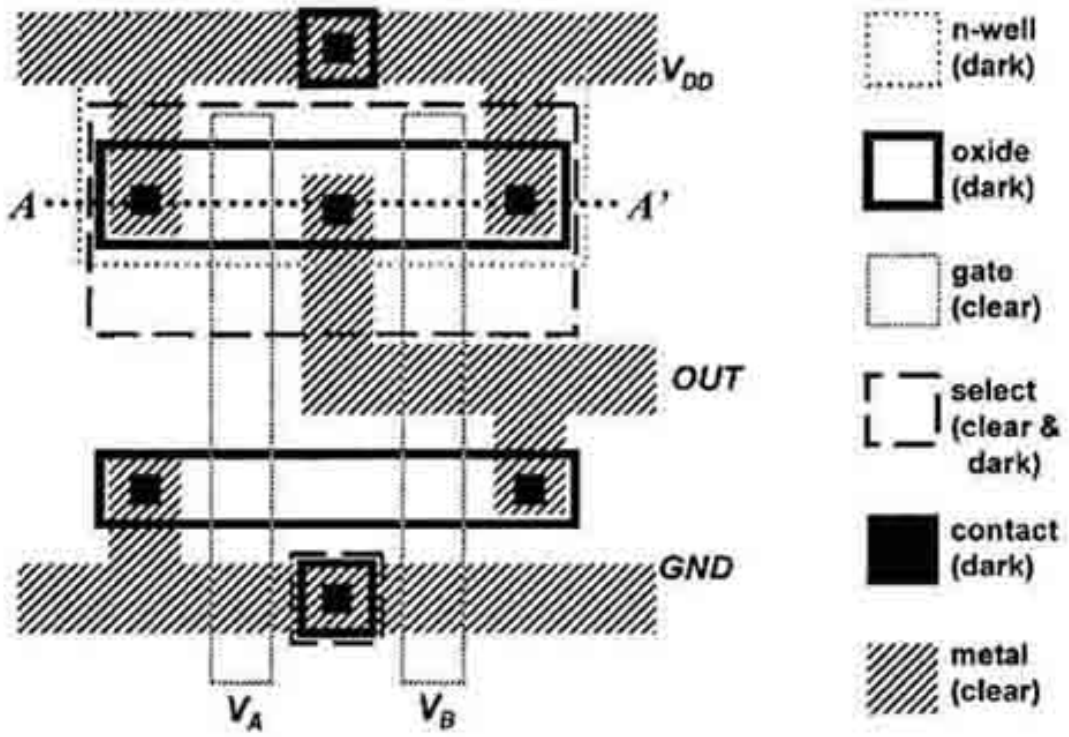


The output C is initially equal to 0, and the output D is initially equal to 1.

For the given **S** and **R** timing diagrams below, draw the timing diagrams (for t>0) for **A**, **B**, **C**, and **D** on the plots provided. **[13 pts]**



Problem 7: CMOS Technology [20 points in total]
The layout of a CMOS logic gate is shown below:



The following fabrication process (starting with a p-type Si wafer) is used:

1. Thermally grow 700 nm of SiO_2.
2. Pattern the SiO_2 using the n-well mask.
3. Implant phosphorous and perform a high-temperature, long anneal to "drive in" the well to a depth of 1 μm.
4. Remove the SiO_2 (using a highly selective wet etch process which does not etch Si).
5. Grow 0.5 μm of SiO_2 ("field oxide").
6. Pattern the SiO_2 using the oxide mask.
7. Thermally grow 10 nm of SiO_2 ("gate oxide") in the bare regions of the Si.
8. Deposit 200nm of poly-Si (by CVD).
9. Pattern the poly-Si using the gate mask.
10. Use clear-field select mask to pattern photoresist; implant phosphorus. This will form the n+ source and drain junctions for the n-channel MOSDETs.
11. Use dark-field select mask to pattern photoresist; implant boron. This will form the p+ source and drain junctions for the p-channel MOSFETs.
12. Thermally anneal the wafer in order to activate the implanted dopants. The final source/drain junction depth is 100nm.
13. Deposit 0.5 μm of SiO_2 ("passivation oxide").
14. Pattern the deposited SiO_2 using the contact mask.
15. Deposit 0.5 μm of aluminum.
16. Pattern the aluminum using the metal mask.

Problem 7 (continued)

a) Draw cross-section A-A' in the space provided. Identify all layers clearly. **[10 pts]**

Cross-section A-A'

b) Draw the circuit schematic, labeling V_{DD}, GND, V_A, V_B, and OUT. **[5 pts]**

Circuit Schematic

c) Assuming that $k_n' = 3k_p'$, would you expect this logic gate to have comparable worst-case "pull-up" and "pull-down" propagation delays? (Is $t_{pLH} \cong t_{pHL}$?) Justify your answer. **[5 pts]**

Problem 8: Technology Scaling (Short-Answer Questions) [10 points in total]

a) Explain how transistor scaling improves both the cost (per function) and performance (circuit operating speed) of CMOS integrated circuits. [5 pts]

b) Explain why interconnect delay is becoming more of a concern as CMOS technology advances. **[5 pts]**